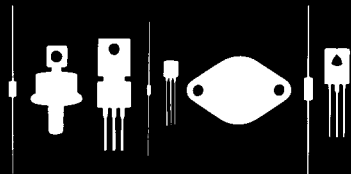


Central
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 145 Adams Avenue
 Hauppauge, New York 11788



MPS8097

NPN SILICON TRANSISTOR

JEDEC TO-92 CASE (EBC)

DESCRIPTION

The CENTRAL SEMICONDUCTOR MPS8097 is an Epoxy Molded Silicon NPN Transistor designed for low noise audio amplifier applications.

MAXIMUM RATINGS (T_A = 25°C)

	<u>SYMBOL</u>		<u>UNITS</u>
Collector-Base Voltage	V _{CB0}	60	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current	I _C	200	mA
Power Dissipation	P _D	625	mW
Operating and Storage			
Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	θ _{JA}	200	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	<u>MIN</u>	<u>MAX</u>	<u>UNITS</u>
I _{CB0}	V _{CB} = 60V		10	μA
I _{CB0}	V _{CB} = 40V		30	nA
I _{EBO}	V _{BE} = 6.0V		20	nA
BV _{CEO}	I _C = 10mA	40		V
V _{BE(ON)}	V _{CE} = 5.0V, I _C = 100μA	0.45	0.65	V
h _{FE}	V _{CE} = 5.0V, I _C = 100μA	250	700	
h _{fe}	V _{CE} = 5.0V, I _C = 100μA, f = 1.0kHz	250	800	
C _{ob}	V _{CB} = 5.0V, I _E = 0, f = 1.0MHz	1.0	4.0	pF
C _{eb}	V _{BE} = 0.5V, I _C = 0, f = 1.0MHz		10	pF
NF	V _{CE} = 5.0V, I _C = 100μA, R _S = 10kΩ, f = 10Hz to 15.7kHz		2.0	dB
e _n	V _{CE} = 5.0V, I _C = 100μA, R _S = 10kΩ, f = 100Hz, BW = 1.0Hz		32	nV/√Hz

CentralTM
Semiconductor Corp.

145 Adams Avenue
 Hauppauge, NY 11788 USA
 Tel: (631) 435-1110 • Fax: (631) 435-1824
 www.centrasemi.com